

BUK9610-100B

N-channel TrenchMOS logic level FET Rev. 03 — 31 January 2011

Product data sheet

1. **Product profile**

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	75	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	300	W
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	8.3	9.7	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11; see Figure 12		-	8.6	10	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 75 \text{ A}; V_{\text{sup}} \le 100 \text{ V};$ $R_{\text{GS}} = 50 \Omega; V_{\text{GS}} = 5 \text{ V};$ $T_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}$	-	-	629	mJ
Dynamic cl	haracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 80 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	32	-	nC

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

_			
Symbol	Description	Simplified outline	Graphic symbol
G	gate		
D	drain[1]	mb	D
S	source		
D	mounting base; connected to drain	ı	<u></u>
		\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	mbb076 S
		1 3	
		SOT404 (D2PAK)	
	G D S	G gate D drain[1] S source	G gate D drain[1] S source D mounting base; connected to drain

^[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9610-100B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		,				
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	100	V
V_{GS}	gate-source voltage			-15	15	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 1}};$	<u>[1]</u>	-	110	Α
		see Figure 3	[2]	-	75	Α
		$T_{mb} = 100 ^{\circ}C; V_{GS} = 5 V; see \underline{Figure 1}$	[2]	-	75	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see Figure 3		-	438	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	300	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
Is	source current	T _{mb} = 25 °C	<u>[1]</u>	-	110	Α
			[2]	-	75	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	438	Α
Avalanche i	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	629	mJ
		* *				

- [1] Current is limited by power dissipation chip rating.
- [2] Continuous current is limited by package.

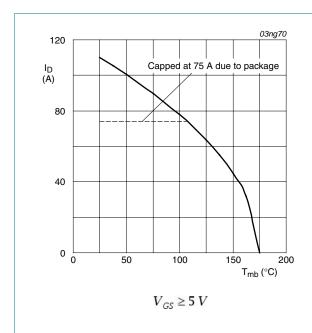


Fig 1. Normalized continuous drain current as a function of mounting base temperature

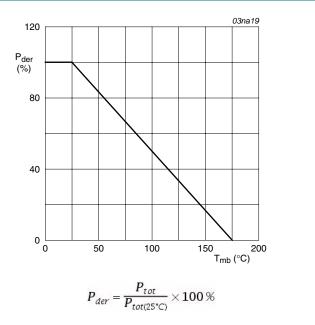
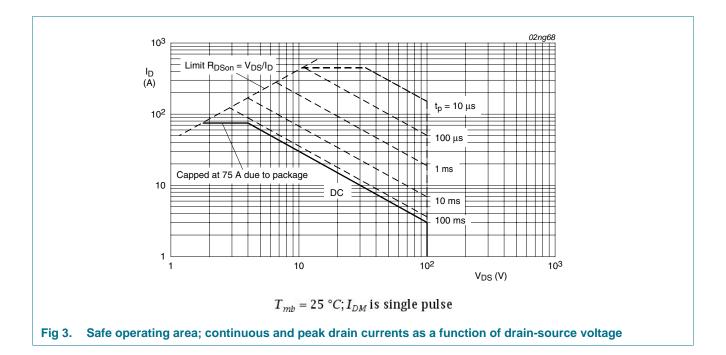


Fig 2. Normalized total power dissipation as a function of mounting base temperature

BUK9610-100B

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W

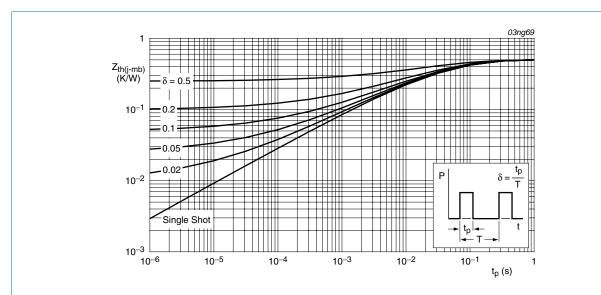


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

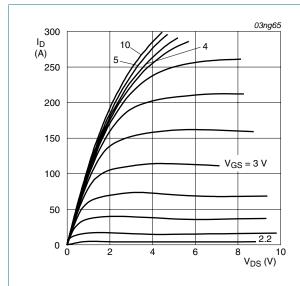
6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
	voltage	$I_D = 0.25$ mA; $V_{GS} = 0$ V; $T_j = -55$ °C	89	-	-	V
V _{GS(th)} gate-source thresho	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 10</u>	1.1	1.5	2	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; see <u>Figure 10</u>	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; see <u>Figure 10</u>	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		V_{GS} = -15 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nΑ
Doon	drain-source on-state resistance	V_{GS} = 5 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	25	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	8.3	9.7	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	-	11	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	8.6	10	mΩ
Dynamic (characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A; } V_{DS} = 80 \text{ V; } V_{GS} = 5 \text{ V;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure } 13}{\text{Figure } 13}$	-	86	-	nC
Q_{GS}	gate-source charge		-	16	-	nC
Q_{GD}	gate-drain charge		-	32	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	8284	11045	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	676	811	pF
C_{rss}	reverse transfer capacitance		-	237	325	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	60	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 ^{\circ}C$	-	110	-	ns
$t_{d(off)}$	turn-off delay time		-	250	-	ns
t _f	fall time	V_{DS} = 30 V; R_L = 1.2 Ω ; V_{GS} 5 V; $R_{G(ext)}$ = 10 Ω ; T_j = 25 °C	-	94	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die; $T_j = 25$ °C	-	4.5	-	nΗ
		from upper edge of drain mounting base to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	in diode					
V_{SD}	source-drain voltage	$I_S = 40 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	78	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	268	-	nC



 $T_j = 25^{\circ}C; t_p = 300\mu s$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

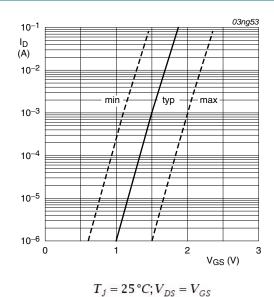
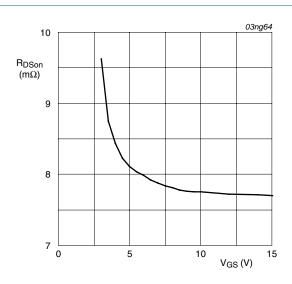
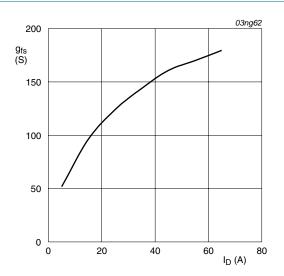


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; I_D = 25A$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j=25^{\circ}C; V_{DS}=25V$

Fig 8. Forward transconductance as a function of drain current; typical values

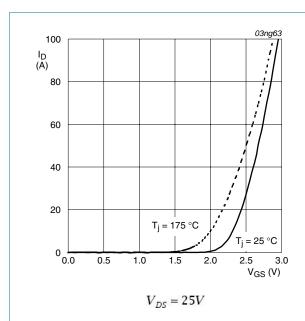


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

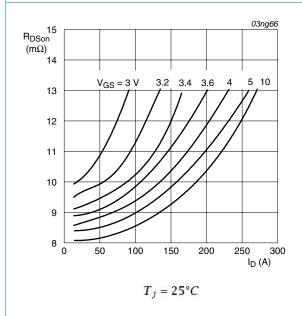
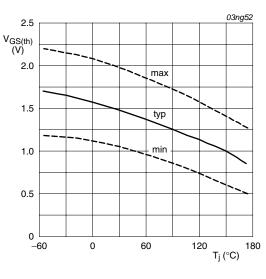


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 1mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

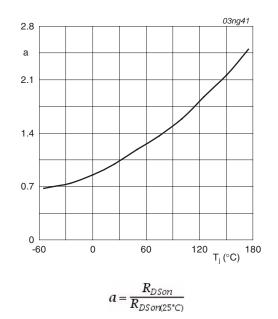


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

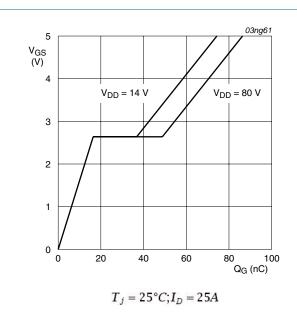
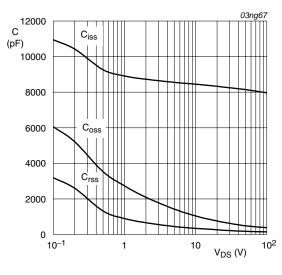
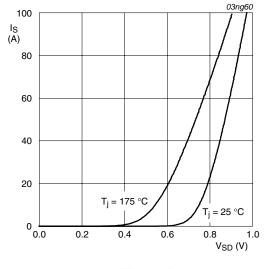


Fig 13. Gate-source voltage as a function of turn-on gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0V$

Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

7. Package outline

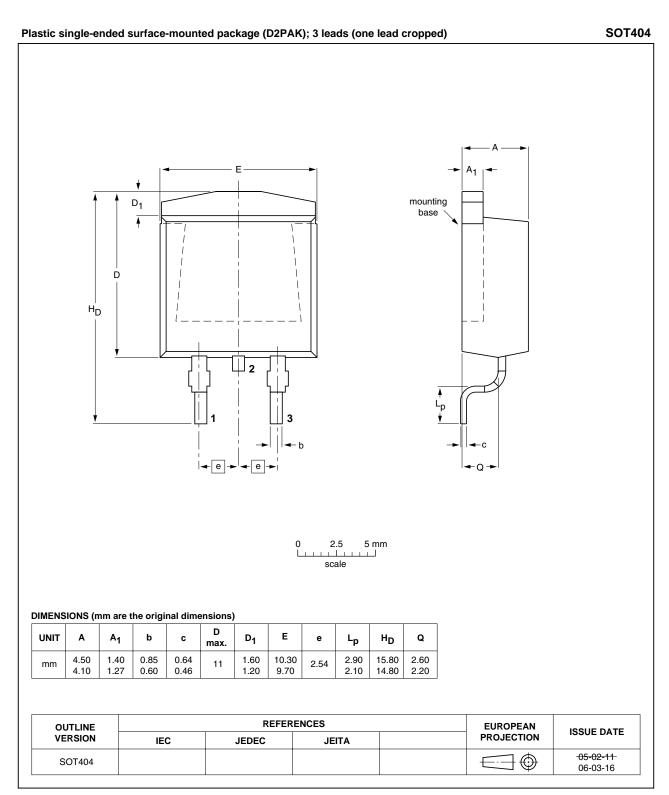


Fig 16. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9610-100B v.3	20110131	Product data sheet	-	BUK95_9610_100B v.2
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 			
 Legal texts have been adapted to the new company name where appropriate. 				nere appropriate.
	 Type number Bl 	JK9610-100B separated	from data sheet BUI	(95_9610_100B v.2.
BUK95_9610_100B v.2	20021008	Product data	-	BUK95_9610-100B v.1

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9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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BUK9610-100B

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N-channel TrenchMOS logic level FET

11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics5
6	Characteristics6
7	Package outline10
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks13
10	Contact information13



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